



UNITED STATES PATENT AND TRADEMARK OFFICE
VERIFICATION OF A TRANSLATION

I, Susan POTTS BA ACIS,

Director of RWS Group plc, of Europa House, Marsham Way, Gerrards Cross,
Buckinghamshire, England, hereby declare that:

My name and post office address are as stated below;

That the translator responsible for the attached translation is knowledgeable in the English language and in the Japanese language, and that, to the best of RWS Group plc knowledge and belief, the English translation of the marked portion of the attached Japanese document is true and complete.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Date: 20 July 2000

Signature of the director:

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AUG - 4 2000

For and on behalf of RWS Group plc

TECHNOLOGY CENTER 2000

Post Office Address :

Europa House, Marsham Way,
Gerrards Cross, Buckinghamshire,
England.

NOTE (The list of cited documents etc. is shown below)

Claims 1 to 10

Cited documents 1 to 3

Remarks

(With regard to Claims 1 to 4)

Cited example 1 discloses the formation of SiOF of a high fluorine concentration in the wiring space and the formation of SiOF of a low fluorine concentration above the wiring (see cited example 1 section [0040]).

Cited example 1 discloses the formation of some SiOF of a high fluorine concentration also above the wiring, and cited example 2 discloses the formation of SiOF of a high fluorine concentration and a low permittivity in the wiring space alone, and so it is perceived that one skilled in the art could have arrived with no difficulty whatsoever at having the SiOF of a high fluorine concentration of cited example 1 in the wiring space alone.

Furthermore, it is perceived that one skilled in the art could, if necessary, arrive at having the fluorine content of the SiOF at the relatively high concentration of 5 atom % in order to lower the permittivity of the wiring space.

(With regard to Claims 5 to 10)

The formation of SiOF by injecting fluorine ions is commonly known technology as disclosed in cited example 3, and so it is perceived that one skilled in

the art could easily arrive at the use of ion injection to form the SiOF of a high fluorine concentration of cited examples 1 and 2.

List of Cited Documents etc.

1. Japanese Unexamined Patent Application No. H10-056009.
2. Japanese Unexamined Patent Application No. H10-022389
3. Japanese Unexamined Patent Application No. H02-077127

Record of the Results of the Prior Arts Search

Technical Fields Searched: Int.Cl. (7) H01L21/31-21/3213
H01L21/768

Prior Art documents: Japanese Unexamined Patent Application No. H9-266207

This record is not a component of the reasons for refusal.